

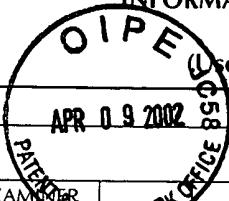
## LIST OF PATENTS AND OTHER ITEMS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

(Use several sheets if necessary)

ATTY. DOCKET NO.  
263/169SERIAL NO.  
10/051,860

APPLICANT:

Eric J. Bergman

FILING DATE:  
January 16, 2002GROUP:  
1446

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PTO-1449

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	TRADEMARK OFFICE	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE
JKS		AA 5,055,138	10/8/91	Slinn			
		AB 5,120,370	6/9/92	Mori et al.			
		AC 5,647,386	7/15/97	Kaiser			
		AD 5,181,985	1/26/93	Lampert et al.			
		AE 5,503,708	4/2/96	Koizumi et al.			
		AF 5,464,480	11/7/95	Matthews			
		AH 5,308,745	5/3/94	Schwartzkopf			
		AI 4,695,327	9/22/87	Grebinski			
		AJ 5,632,847	5/27/97	Ohno et al.			
		AK 5,911,837	6/15/99	Matthews			
		AL 5,705,089	1/6/98	Sugihara et al.			
		AM 5,244,000	9/14/93	Stanford et al.			
		AN 5,714,203	2/3/98	Schellenberger et al.			
		AO 5,896,875	4/27/99	Yoneda			
		AP 4,974,530	12/4/90	Lyon			
		AQ 5,248,380	9/28/93	Tanaka			
		AR 5,520,744	5/28/96	Fujikawa et al.			
		AS 5,415,191	5/16/95	Mashimo et al.			
		AT 5,658,615	8/19/97	Hasebe et al.			
		AU 5,858,107	1/12/99	Chao et al.			
		AV 5,235,995	8/17/93	Bergman et al.			
JKS		AW 5,378,317	1/3/95	Kashiwase et al.			

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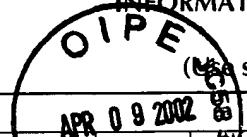
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ITEM	AX	971,368	10/26/99	Nelson et al.	1700
	AY	5,234,540	8/10/93	Grant et al.	
	AZ	5,803,982	9/8/98	Kosofsky et al.	
	BA	5,944,907	8/31/99	Ohmi	
	BB	5,232,511	8/3/93	Bergman	
	BC	5,776,296	7/7/98	Matthews	
	BD	5,071,485	12/10/91	Matthews et al.	
	BE	4,778,532	10/18/88	McConnell et al.	
	BF	4,899,767	1/13/90	McConnell et al.	
	BG	5,964,954	10/12/99	Matsukawa et al.	
	BH	5,032,218	7/16/91	Dobson	
	BI	6,249,933	6/2001	Bergman	
	BJ	6,267,125	7/2001	Bergman et al.	
	BK	6,273,108	8/2001	Bergman et al.	
	BL	5,950,643	9/1999	Miyazaki et al.	
	BM	6,146,469	11/2000	Toshima	
	BN	4,917,123	4/90	McConnell et al.	
	BO	5,105,556	4/92	Kurokawa et al.	
	BP	5,326,406	7/94	Kaneko et al.	
	BQ	4,186,032	1/80	Ham	
	BR	4,749,440	6/88	Blackwood et al.	
	BS	4,817,652	4/89	Liu	
	BT	5,832,177	11/98	Shinagawa et al.	
78	BU	5,964,952	10/99	Kunze-Concewitz	

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ATTY. DOCKET NO.  
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10/051,661APPLICANT:  
Eric J. BergmanFILING DATE:  
January 16, 2002

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146

10 2002

708	BW	5,503,708	4/96	REEDMAN et al.	700
	BX	5,378,317	1/95	Kashiwase et al.	
708	BY	5,571,367	11/96	Nakajima et al.	

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION YES      NO
708	BZ	0 548 596 A2	6/3/93	Europe			
	CA	0 344 764	12/6/89	Europe			
	CB	0 702 399	3/20/96	Europe			
	CC	GB 2 287 827	9/27/95	United Kingdom			
	CD	JP52-12063		Japan			
	CE	JPO 4 301 145		Japan			
	CF	EP 587 889		EPO			
	CG	JP 401042129		Japan			
	CH	WO 99/52654	10/21/99	PCT			
708	CI	WO 01/07177 A1	2/1/01	PCT			

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

708	CJ	Abstract of JP 3041729 published 2/22/91
	CK	Abstract of JP 1008630, published 1/12/89
	CL	Abstract of Japanese Appln. No. 63-16127 published July 31, 1989.
	CM	Abstract of Japanese Appln. No. 52-100473 published March 14, 1979.
	CN	Abstract of Japanese Appln. No. 1-192712 published March 12, 1992.
708	CO	Translation/Abstract of Japanese Appln. No. 1984-125760 published January 10, 1986.

EXAMINER:

708 Liner

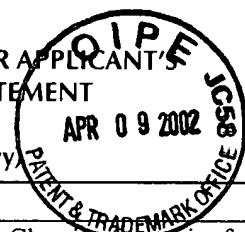
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10/051,860APR  
APPLICANT:  
Eric J. BergmanFILING DATE:  
January 16, 2002GROUP:  
1746

NJS	CP	Heyns, M.M., et al. "New Wet Cleaning Strategies for Obtaining Highly Reliable Thin Oxides," MRP Symposium Proceedings on Materials Research Society, Spring Meeting, San Francisco, CA April 13-15, 1993, p. 35 (1993)
	CQ	Adler, Marilyn Grace and Hall, George Richard, "The Kinetics and Mechanism of Hydroxide Ion Catalyzed Ozone Decomposition in Aqueous Solution" <i>J.Am.Chem.Soc.</i> , Volume 72, pp. 1884-86, 1950.
	CR	Nelson, Steve, "Ozonated water for photoresist removal" <i>Solid State Technology</i> , pp. 107-112 (July 1999)
	CS	Christenson, Kurt K., et al. "Deionized Water Helps Remove Wafer Stripping 'Resist'-ance," <a href="http://www.precisioncleaningweb.com">www.precisioncleaningweb.com</a> - <i>Precision Cleaning Web - Archives</i> , pp. 10-20 (April 1998)
	CT	Sehested, K., et al., "Decomposition of Ozone in Aqueous Acid Solutions (pH 0-4)," <i>J. Phys. Chem.</i> , pp. 1005-1009 (1992)
	CU	Krusell, W.C. et al., "Cleaning Technology for High Volume Production of Silicon Wafers," <i>ECS Proc. of the First Int'l. Symposium on Cleaning Technology I Semiconductor Device Mfg.</i> , pp. 23-32 (October 1989)
	CV	Vig, John R., "UV/Ozone Cleaning of Surfaces," <i>U.S. Army Elec. Tech. and Devices Lab.</i> , pp. 1-26
	CW	Vig, John R., "UV/Ozone Cleaning of Surfaces: A Review," <i>Surface Contamination: Genesis, Detection, and Control</i> , pp. 235-253(1979)
	CX	Tong, Jeremy, et al., "Aqueous Ozone Cleaning of Silicon Wafers," <i>ECS Extended Abstracts</i> , Phoenix, AZ, Abstract No. 506, pp. 753 (October 13-17, 1991)
	CY	Zafonte, Leo, et al., "UV/Ozone Cleaning For Organics Removal on Silicon Wafers," <i>SPIE Optical Microlithography III: Technology for the Next Decade</i> , Vol. 470, pp. 164-175 (1984)
	CZ	Baumgärtner, H., et al., "Ozone Cleaning of the Si-SiO <sub>2</sub> System," <i>Appl. Phys. A</i> , Vol. 43, pp. 223-226 (1987)
	DA	Isagawa, Tatsuhiko, et al., "Ultra Clean Surface Preparation Using Ozonized Ultrapure Water," <i>Extended Abstracts of the 1982 Int'l. Conf. on Solid State Devices and Materials</i> , pp. 193-195 (1992)
	DB	Shimada, H., et al., "Residual-Surfactant-Free Photoresist Development Process," <i>J. Electrochem. Soc.</i> , 139(6):1721-1730 (June 1992)
	DC	Tong, Jeremy K. et al., "Aqueous Ozone Cleaning of Silicon Wafers," <i>Proc. of 2<sup>nd</sup> Int'l. Symposium on Cleaning Tech. In Semiconductor Device Mfg.</i> , pp. 18-25 (October 1992)
	DD	Tong, Jeremy K., et al., "Aqueous Ozone Cleaning of Silicon Wafers," <i>Res. Soc. Symp.</i> , pp. 18-25 (1993)
	DE	Ohmi, T., et al., "Native Oxide Growth and Organic Impurity Removal on Si Surface with Ozone-Injected Ultrapure Water," <i>J. Electrochem. Soc.</i> , 140(3):804-810 (March 1993)
	DF	Vig, John R., et al., "UV/Ozone Cleaning of Surfaces," <i>IEEE Transactions on Parts, Hybrids, and Packaging</i> , Vol. PHP-12(4):365-370 (December 1976)
	DG	Vig, John R., "UV/ozone cleaning of surfaces," <i>U.S. Army Electronics Technology and Devices Laboratory, ERADCOM, Ft. Monmouth, NJ</i> , 07703-5302, pp. 1027-1034 (September/October 1984)
	DH	Tabe, Michiharu, "UV ozone cleaning of silicon substrates in silicon molecular beam epitaxy," <i>Appl. Phys. Lett.</i> , 45(10):1073-1075 (November 1984)
	DI	Zazzera, L.A., et al., "XPS and SIMS Study of Anhydrous HF and UV/Ozone-Modified Silicon (100) Surfaces," <i>J. Electrochem. Soc.</i> , 136(2):484-491 (February 1989)
	DJ	Gabriel, Calvin, et al., "Reduced Device Damage Using An Ozone Based Photoresist Removal Process," <i>SPIE Advances in Resist Technology and Processing VI</i> , Vol. 1086, pp. 598-604 (1989)
NJS	DK	Suemitsu, Maki, et al., "Low Temperature Silicon Surface Cleaning by HF Etching/Ultraviolet Ozone Cleaning (HF/UVOC) Method (I) -Optimization of the HF Treatment-," <i>Japanese Journal of Applied Physics</i> , 28(12):2421-2424 (December 1989)

EXAMINER:

*NJS Turner*

DATE CONSIDERED:

*8/12/03*

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263/169S/N NO.  
107051,860APPLICANT:  
Eric J. BergmanFILING DATE:  
January 16, 2002APR 17 2002  
GROUP: 2002  
1746

<i>PHS</i>	DL	Kern, Werner, "The Evolution of Silicon Cleaning Technology," <i>J. Electrochem. Soc.</i> , 137(6):1887-1892 (June 1990)
	DM	Kasi, S.R., et al., "Surface Hydrocarbon Removal from Si by UV/Ozone," <i>ECS Extended Abstracts</i> , No. 458, pp. 691-692 (199)
	DN	Kasi, Srinandan R., et al., "Vapor phase hydrocarbon removal for Si processing," <i>Appl. Phys. Lett.</i> , 57(20):2095-2097 (November 1990)
	DO	Huynh, Cuc K., et al., "Plasma versus ozone photoresist ashing: Temperature effects on process-induced mobile contamination," <i>J. Vac. Sci. Technol.</i> , B9(2):353-356 (Mar/Apr 1991)
	DP	Bedge, Satish, et al., "Kinetics of UV/O <sub>2</sub> Cleaning and Surface Passivation Experiments and Modeling," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 259, pp. 207-212 (1992)
	DQ	Goulding, M.R., "The selective epitaxial growth of silicon," <i>Materials Science and Engineering</i> , Vol. B17, pp. 47-67 (1993)
	DR	Ganesan, Gans S., et al., "Characterizing Organic Contamination in IC Package Assembly," <i>The Int'l. Soc. for Hybrid Microelectronics</i> , Vol. 17, #2, Second Quarter, pp. 152-160 (1994)
	DS	Egitto, F.D., et al., "Removal of Poly(Dimethylsiloxane) Contamination From Silicon Surfaces With UV/Ozone Treatment," <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 385, pp. 245-250 (1995)
	DT	Amick, J.A., "Cleanliness and the Cleaning of Silicon Wafers," <i>Solid State Technology</i> , pp. 47-52 (November 1976)
	DU	Bolon, D.A., et al., "Ultraviolet Depolymerization of Photoresist Polymers," <i>Polymer Engineering and Science</i> , 12(2):108-111 (March 1972)
	DV	Krusell, W.C., et al., "The Characterization of Silicon Substrate Cleaning Treatments by use of SIMS and MOS Electrical Testing," <i>ECS Extended Abstracts</i> , No. 229, p. 331-332 (1986)
	DW	Golland, D.E., et al., "The Clean Module: Advanced Technology for Processing Silicon Wafers," <i>Semiconductor Int'l.</i> , pp. 184-187 (September 1987)
	DX	Anantharaman, Ven, Ph.D., et al., "ORGANICS: Detection and Characterization of Organics in Semiconductor DI Water Processes," <i>Ultrapure Water</i> , pp. 30-36 (April 1994)
	DY	"Ozone Concentration Measurement In A Process Gas," <i>Proposed IOA Pan American Group Guideline</i> , pp. 1-21 (December 1993)
<i>PHS</i>	DZ	"Ozone for Semiconductor Applications," <i>Sorbios</i> , pp. 1-6 (October 1991)

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